



2SK3746

N-Channel Power MOSFET 1500V, 2A, 13Ω, TO-3P-3L

ON Semiconductor®

<http://onsemi.com>

Features

- Low ON-resistance, low input capacitance, ultrahigh-speed switching
- High reliability (Adoption of HVP process)
- Avalanche resistance guarantee

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		1500	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		2	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	4	A
Allowable Power Dissipation	P _D		2.5	W
		T _C =25°C	110	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	E _{AS}		41	mJ
Avalanche Current *2	I _{AV}		2	A

*1 V_{DD}=50V, L=20mH, I_{AV}=2A (Fig.1)

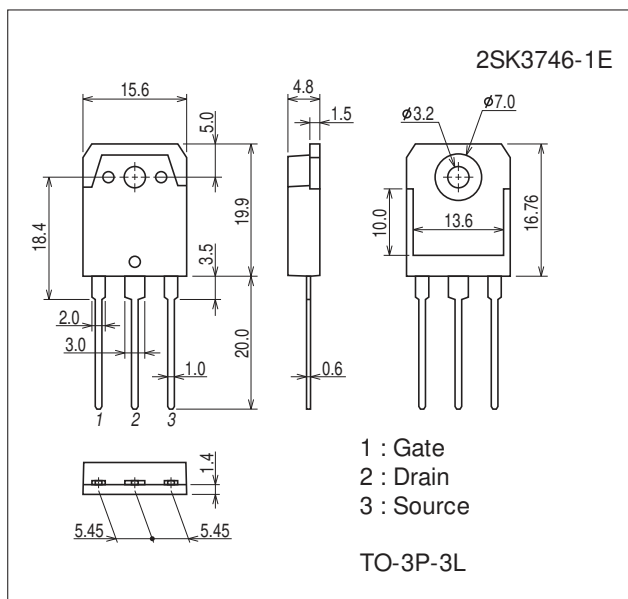
*2 L≤20mH, single pulse

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ)

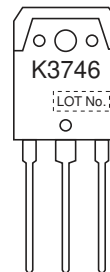
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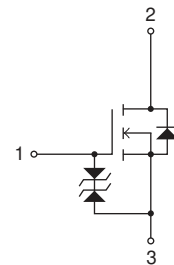
Product & Package Information

- Package : TO-3P-3L
- JEITA, JEDEC : SC-65, TO-247, SOT-199
- Minimum Packing Quantity : 30 pcs./magazine

Marking



Electrical Connection



2SK3746

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit	
			min	typ	max		
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1mA, V_{GS}=0V$	1500			V	
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=1200V, V_{GS}=0V$			100	μA	
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=16V, V_{DS}=0V$			± 10	μA	
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	2.5		3.5	V	
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=20V, I_D=1A$	0.7	1.4		S	
Static Drain-to-Source On-State Resistance	$R_{DS(on)}$	$I_D=1A, V_{GS}=10V$		10	13	Ω	
Input Capacitance	C_{iss}	$V_{DS}=30V, f=1MHz$		380		pF	
Output Capacitance	C_{oss}				70		pF
Reverse Transfer Capacitance	C_{rss}				40		pF
Turn-ON Delay Time	$t_d(on)$	See Fig.2		12		ns	
Rise Time	t_r				37		ns
Turn-OFF Delay Time	$t_d(off)$				152		ns
Fall Time	t_f				59		ns
Total Gate Charge	Q_g	$V_{DS}=200V, V_{GS}=10V, I_D=2A$		37.5		nC	
Gate-to-Source Charge	Q_{gs}				2.7		nC
Gate-to-Drain "Miller" Charge	Q_{gd}				20		nC
Diode Forward Voltage	V_{SD}	$I_S=2A, V_{GS}=0V$		0.88	1.2	V	

Fig.1 Avalanche Resistance Test Circuit

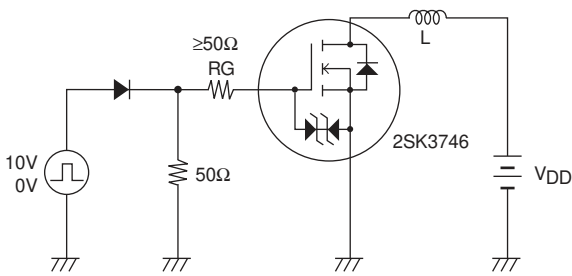
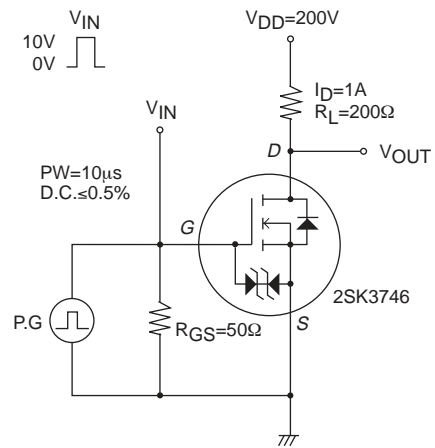
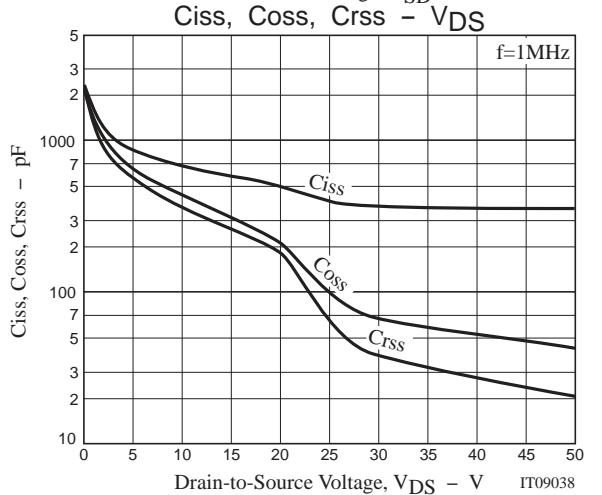
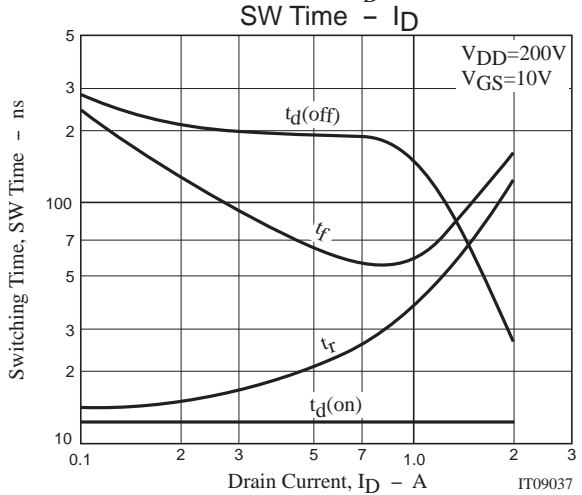
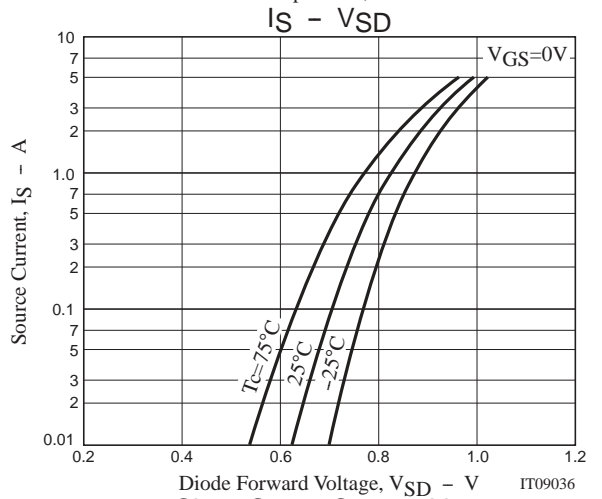
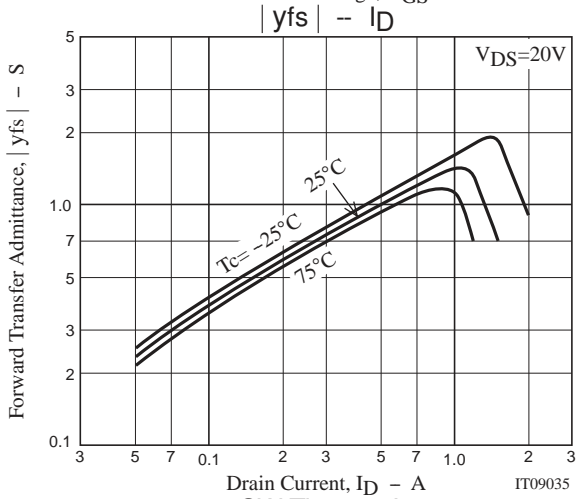
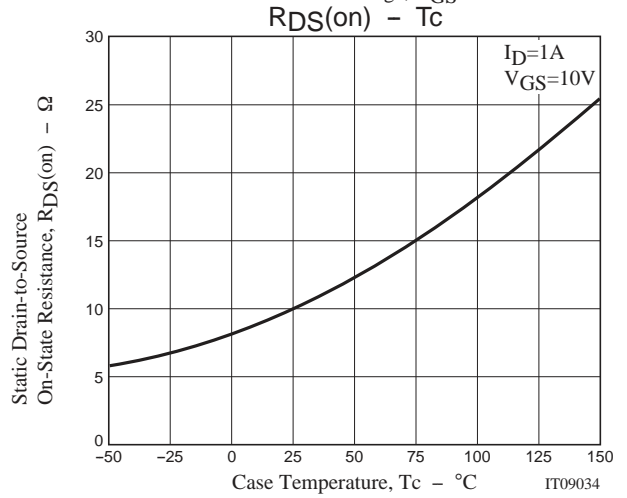
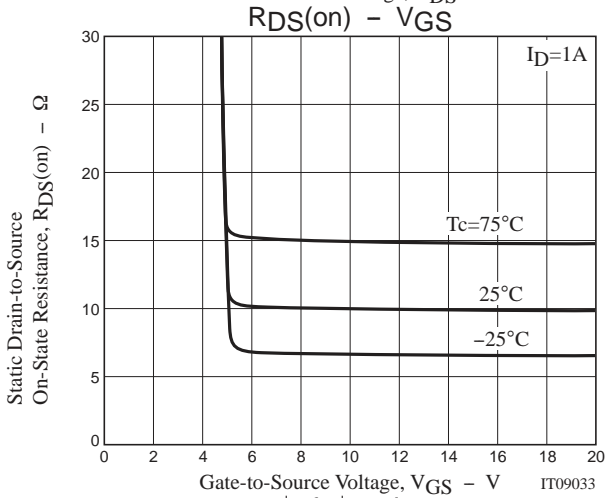
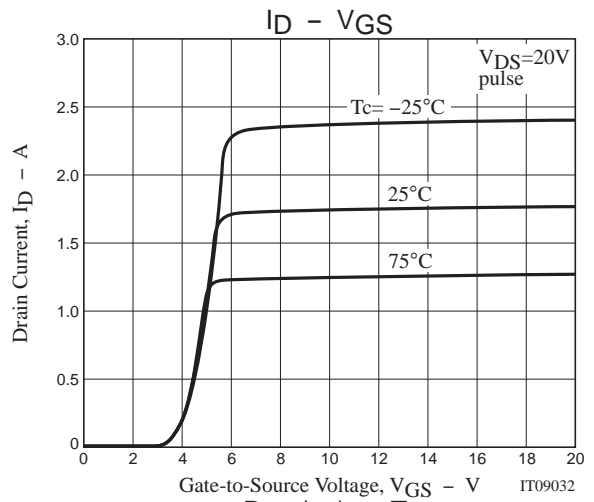
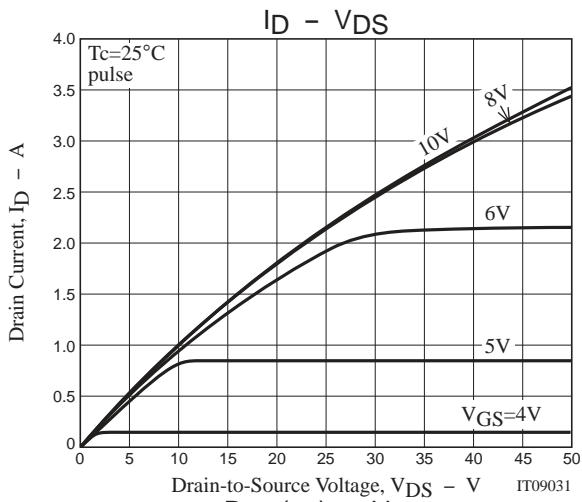


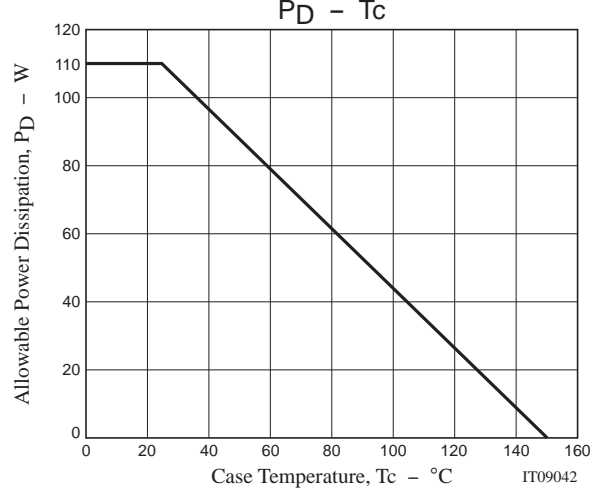
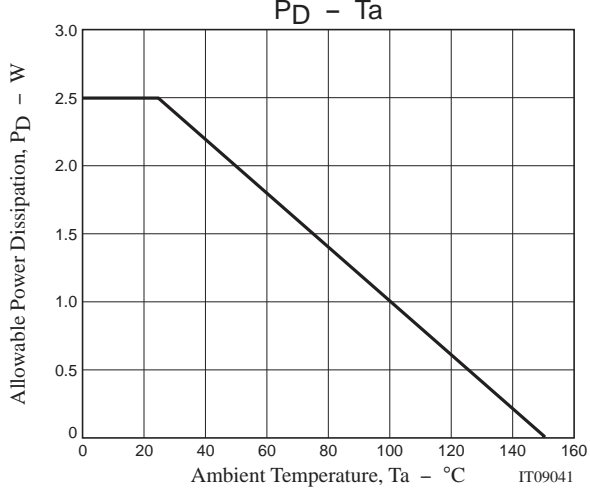
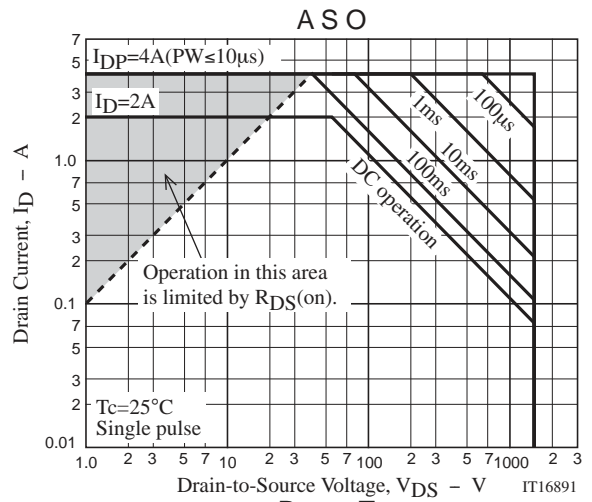
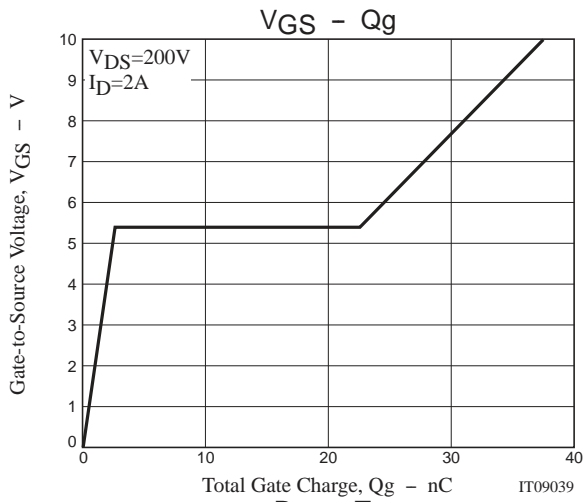
Fig.2 Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
2SK3746-1E	TO-3P-3L	30pcs./magazine	Pb Free





Magazine Specification

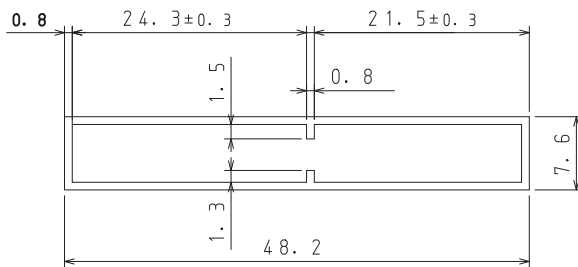
2SK3746-1E

1. Packing Format

Package Name	Maximum Number of devices contained (pcs)			Packing format	
	Magazine	Inner box	Outer box	Inner BOX	Outer BOX
TO-3P-3L	30	450	1800	SPD-0V0001 15 magazines contained Dimensions:mm (external) 568×150×55	SPD-LV0010 4 inner boxes contained Dimensions:mm (external) 590×225×178

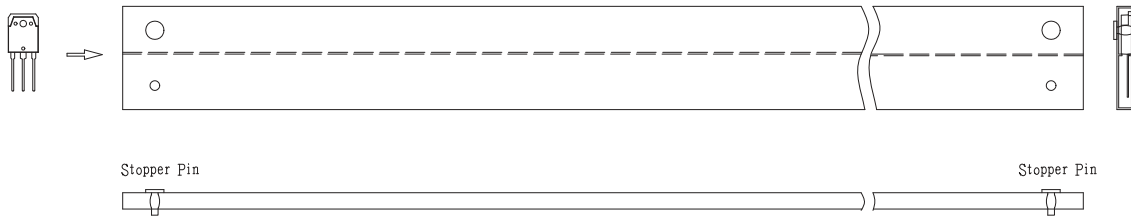
2. Magazine dimensions

(unit:mm)



Tolerance=±0.2mm
 Thickness=0.8±0.2mm
 Length =508.0±1mm
 Material =PVC or PET
 (Antistatic treatment)

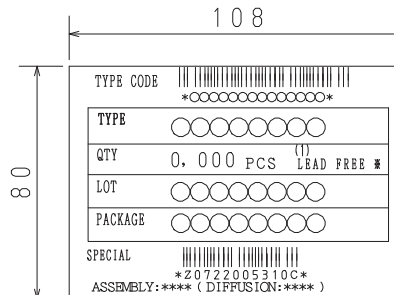
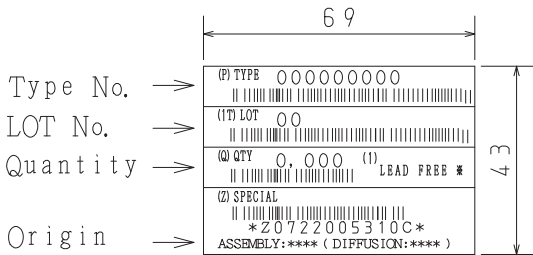
3. Storage method to magazine



4. Inner box label (unit:mm)

5. Outer box label (unit:mm)

It is a label at the time of factory shipments.
 The form of a label may change in physical distribution process.



NOTE (1)

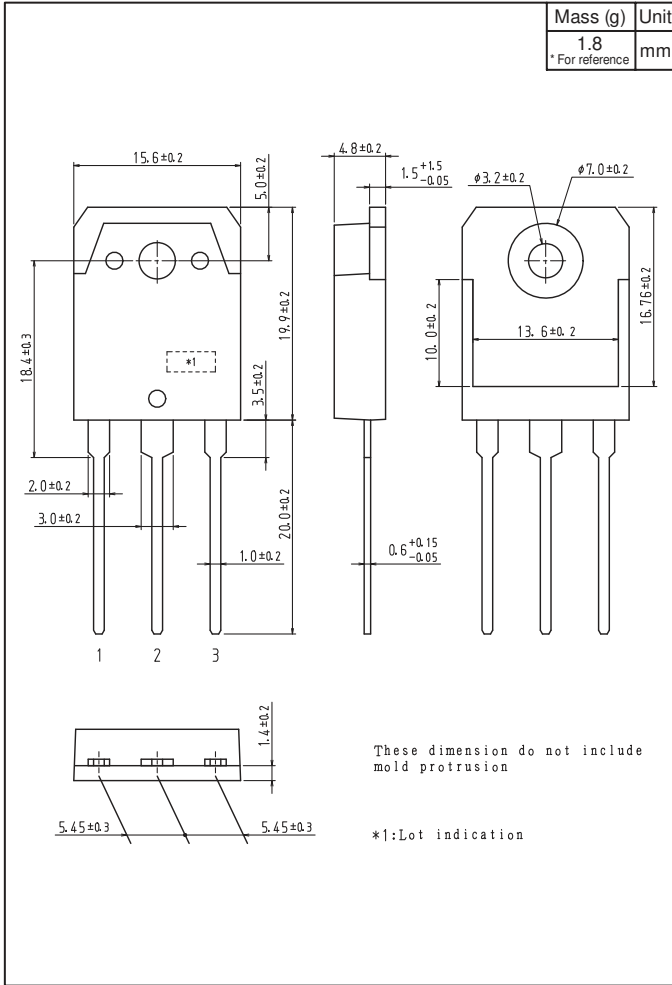
The LEAD FREE * description shows that the surface treatment of the terminal is lead free,

Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A

Outline Drawing

2SK3746-1E

Mass (g)	Unit
1.8	mm
* For reference	



Note on usage : Since the 2SK3746 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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